

isc Silicon NPN Power Transistor

2SC2707

DESCRIPTION

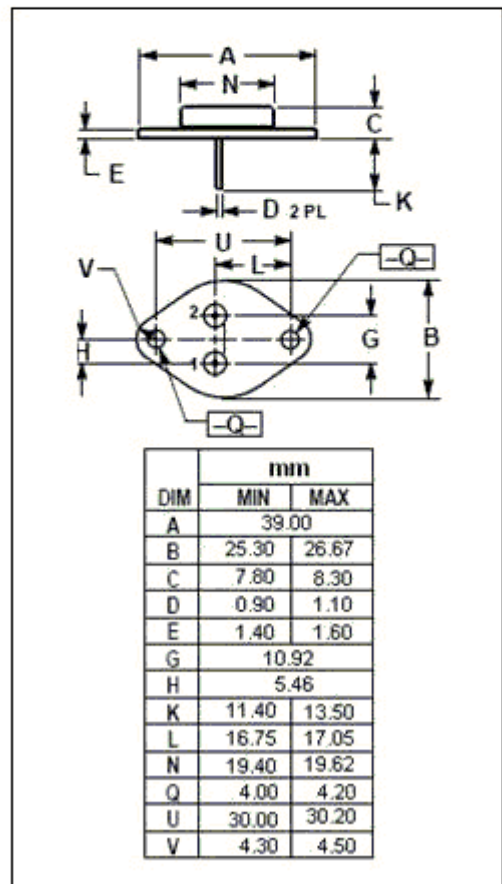
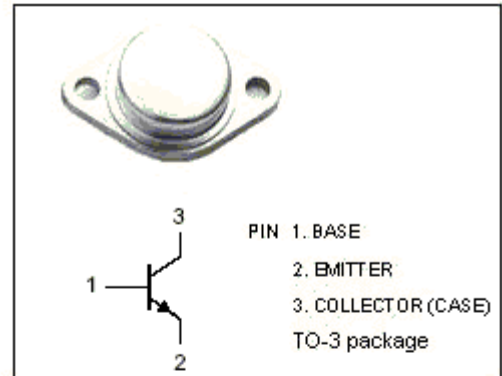
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 180V(\text{Min.})$
- High Power Dissipation
- Complement to Type 2SA1147

APPLICATIONS

- Designed for power switching amplifier and general purpose applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	180	V
$V_{CEO}$	Collector-Emitter Voltage	180	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	15	A
$I_B$	Base Current-Continuous	5	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	150	W
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-65~150	$^\circ\text{C}$



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## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	180			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	180			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 1A			3.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 180V; I <sub>E</sub> = 0			100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 5V	55		160	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 5A ; V <sub>CE</sub> = 5V	30			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 12V		80		MHz